



## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	55	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	
$I_D^*$	Continuous Drain Current	$V_{GS}=4.5V$	A
$I_{DM}^*$	300 $\mu\text{s}$ Pulsed Drain Current		
$I_S^*$	Diode Continuous Forward Current	8	
$T_J$	Maximum Junction Temperature	1	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	150	
$P_D^*$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	W
		$T_A=100^\circ\text{C}$	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient	0.83	$^\circ\text{C/W}$
		0.3	
		150	

Note : \*Surface Mounted on 1in<sup>2</sup> pad area,  $t \leq 10\text{sec}$ .

## Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu\text{A}$	55	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=44V, V_{GS}=0V$ $T_J=85^\circ\text{C}$	-	-	1	$\mu\text{A}$
			-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	0.6	1.3	2	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
$R_{DS(ON)}^a$	Drain-Source On-State Resistance	$V_{GS}=4.5V, I_{DS}=2.1A$	-	90	130	m $\Omega$
		$V_{GS}=2.5V, I_{DS}=1.5A$	-	140	180	
<b>Diode Characteristics</b>						
$V_{SD}^a$	Diode Forward Voltage	$I_{SD}=1A, V_{GS}=0V$	-	0.8	1.1	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=2.1A, dI_{SD}/dt=100A/\mu\text{s}$	-	21	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	16	-	nC

## Electrical Characteristics (Cont.) (T<sub>A</sub> = 25°C unless otherwise noted)

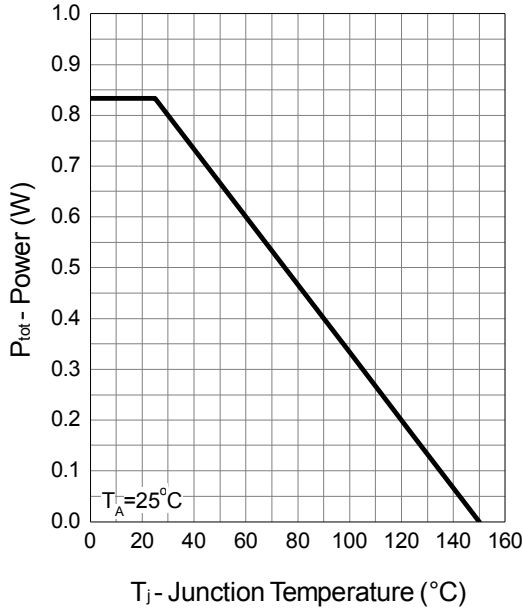
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic Characteristics<sup>b</sup></b>						
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	-	2	-	Ω
C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, Frequency=1.0MHz	-	450	-	pF
C <sub>OSS</sub>	Output Capacitance					
C <sub>RSS</sub>	Reverse Transfer Capacitance					
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>DD</sub> =30V, R <sub>L</sub> =30Ω, I <sub>DS</sub> =1A, V <sub>GEN</sub> =10V, R <sub>G</sub> =6Ω	-	7	13	ns
T <sub>r</sub>	Turn-on Rise Time					
t <sub>d(OFF)</sub>	Turn-off Delay Time					
T <sub>f</sub>	Turn-off Fall Time					
<b>Gate Charge Characteristics<sup>b</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>DS</sub> =2.1A	-	11	16	nC
Q <sub>gs</sub>	Gate-Source Charge					
Q <sub>gd</sub>	Gate-Drain Charge					

Note a : Pulse test ; pulse width ≤ 300μs, duty cycle ≤ 2%.

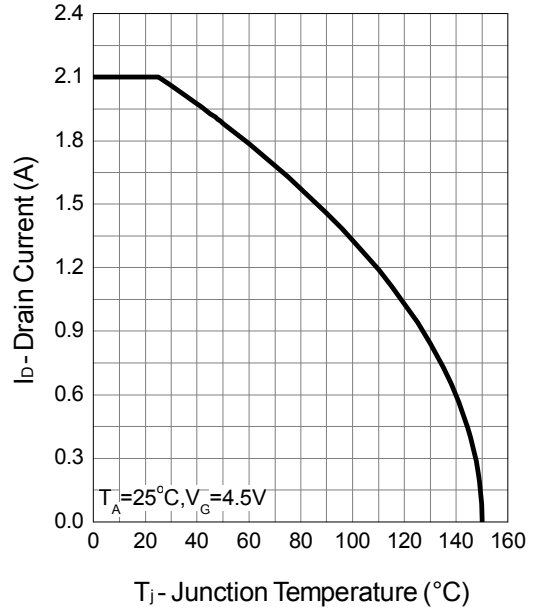
Note b : Guaranteed by design, not subject to production testing.

## Typical Operating Characteristics

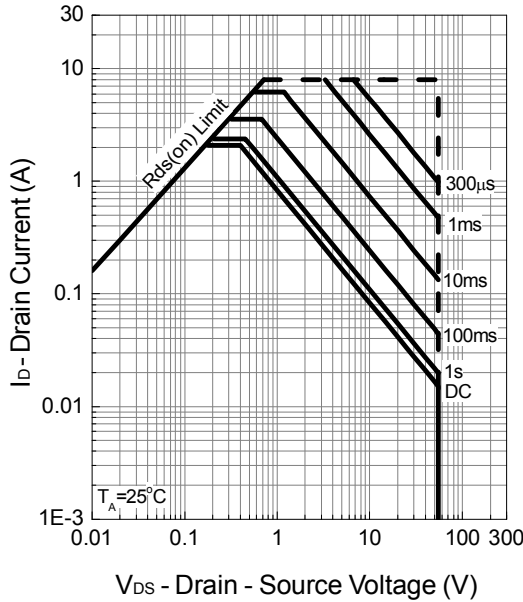
Power Dissipation



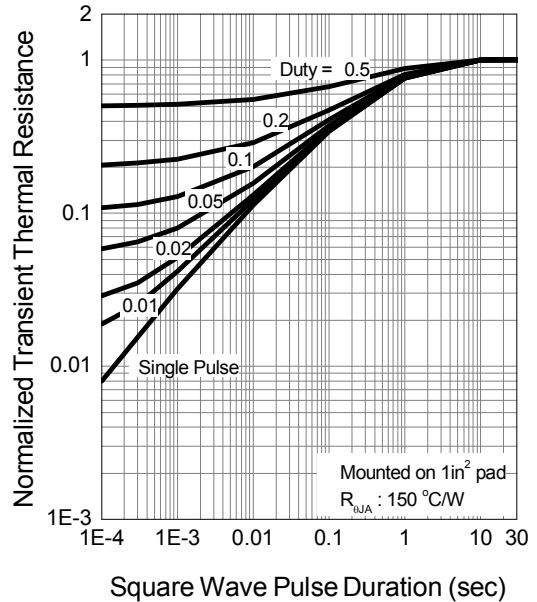
Drain Current



Safe Operation Area

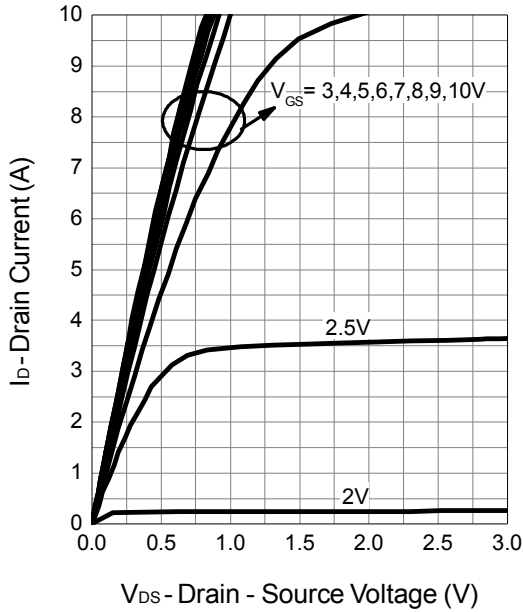


Thermal Transient Impedance

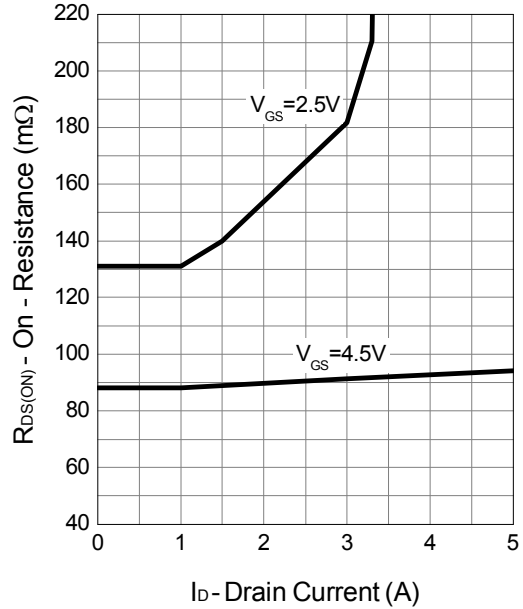


Typical Operating Characteristics (Cont.)

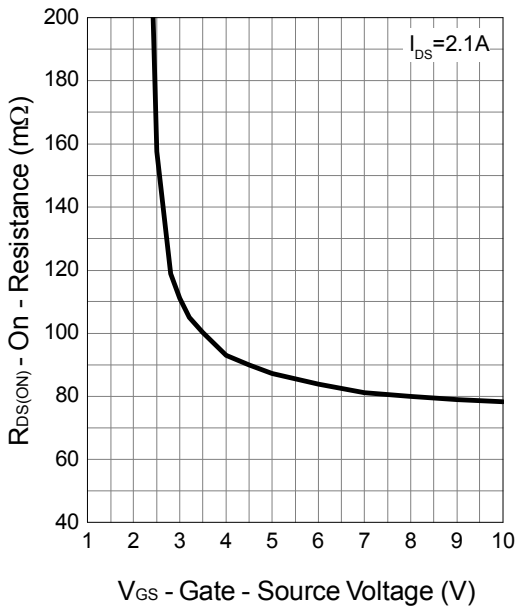
Output Characteristics



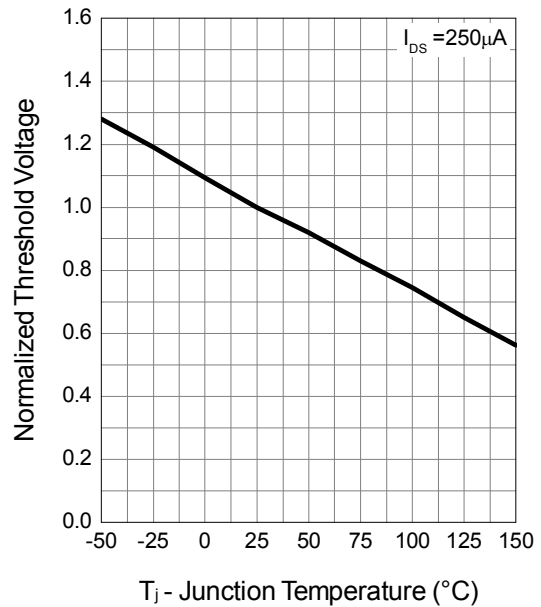
Drain-Source On Resistance



Gate-Source On Resistance

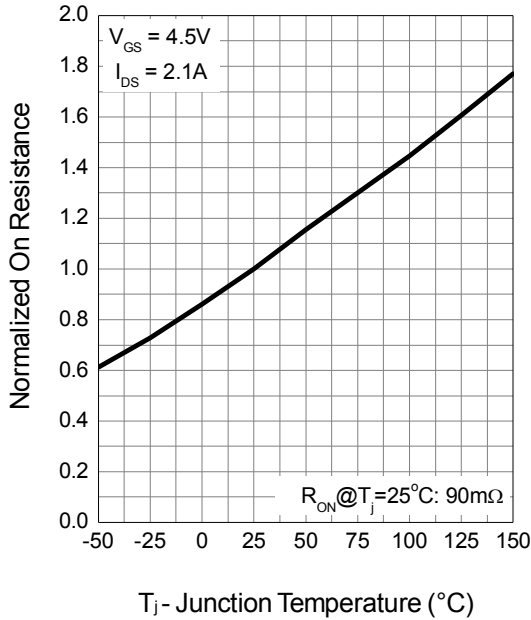


Gate Threshold Voltage

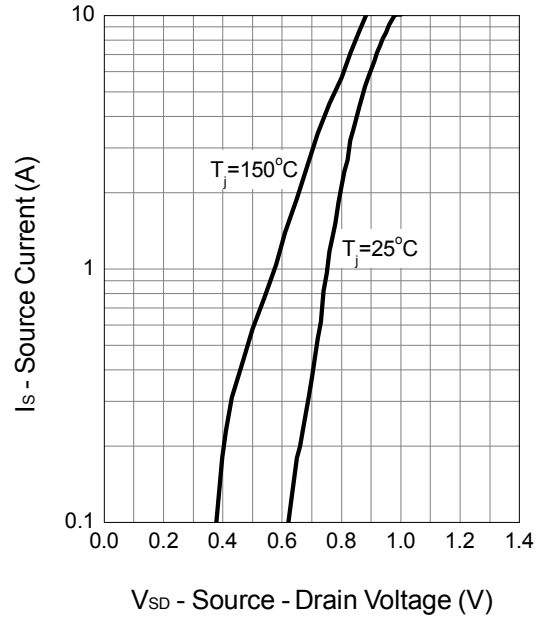


Typical Operating Characteristics (Cont.)

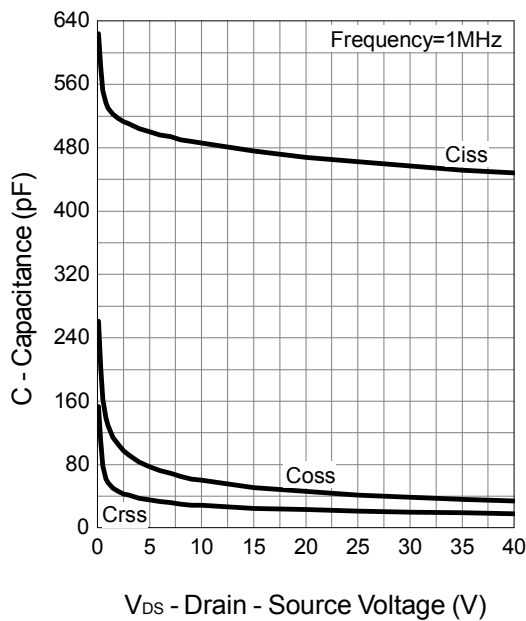
Drain-Source On Resistance



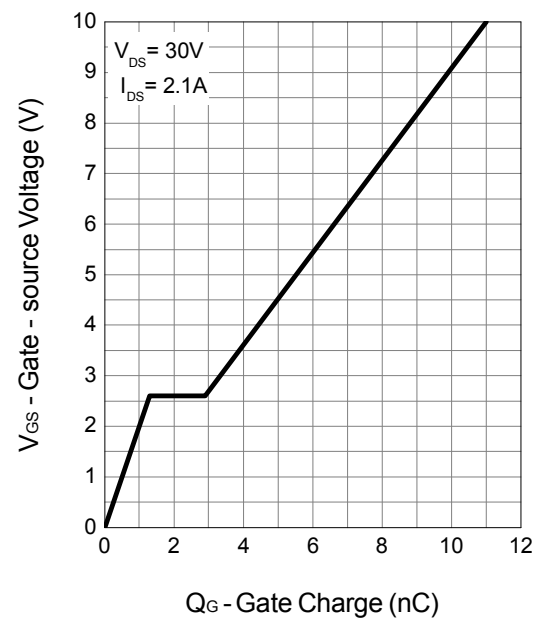
Source-Drain Diode Forward



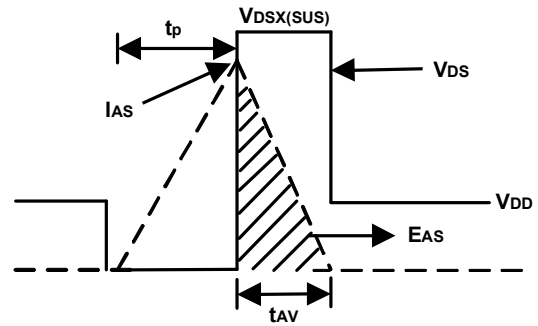
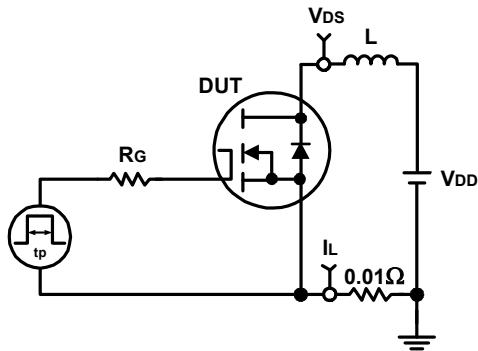
Capacitance



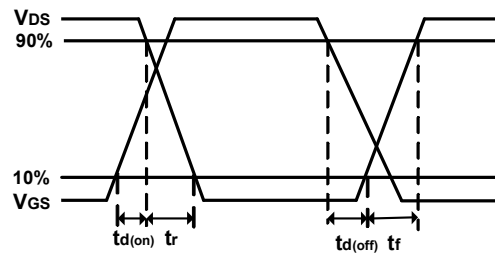
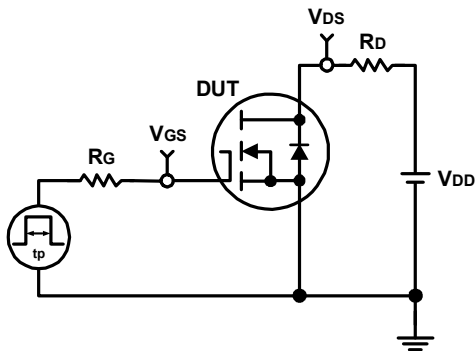
Gate Charge



### Avalanche Test Circuit and Waveforms

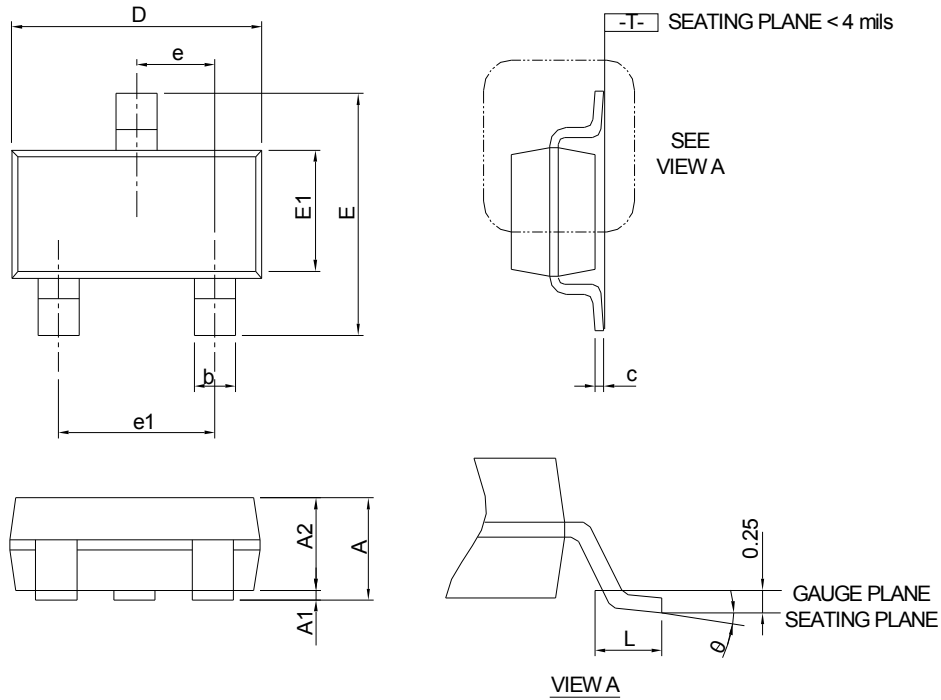


### Switching Time Test Circuit and Waveforms



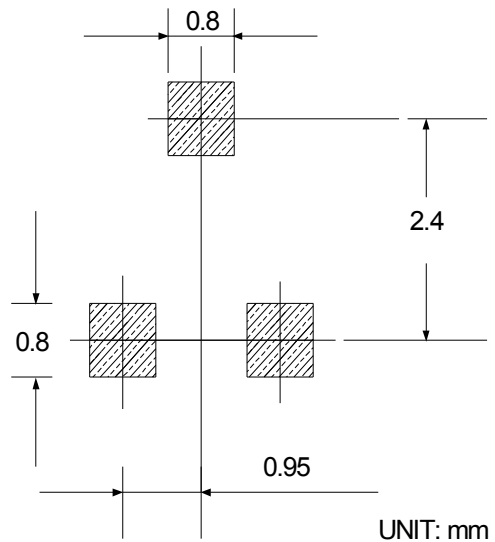
## Package Information

SOT-23-3



SYMBOL	SOT-23-3			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.20	-	0.047
A1	0.00	0.08	0.000	0.003
A2	0.90	1.12	0.035	0.044
b	0.30	0.50	0.012	0.020
c	0.08	0.22	0.003	0.009
D	2.70	3.10	0.106	0.122
E	2.60	3.00	0.102	0.118
E1	1.40	1.80	0.055	0.071
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
θ	0°	8°	0°	8°

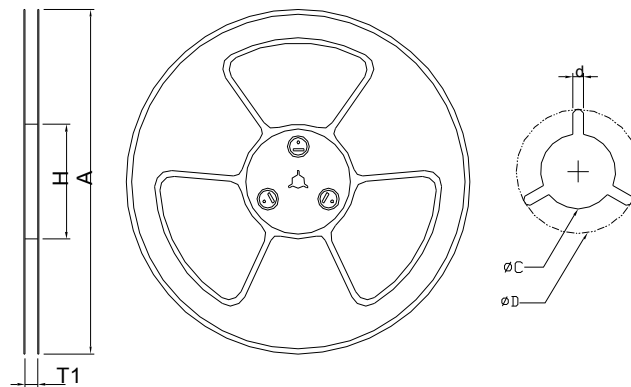
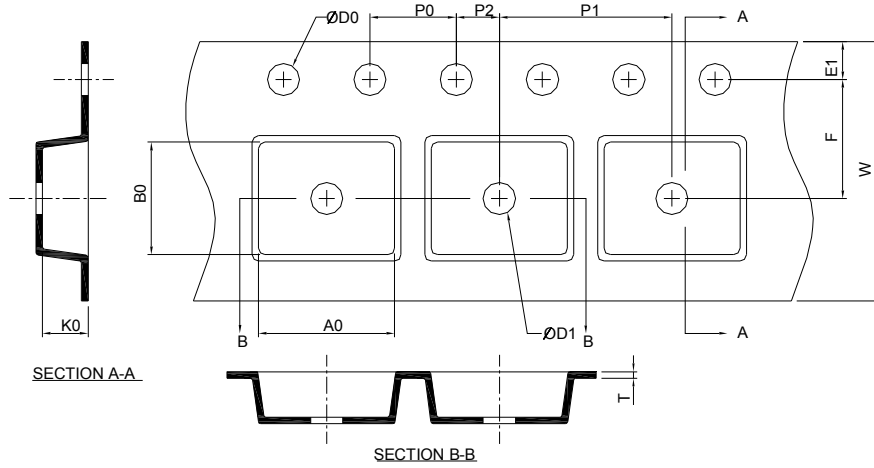
### RECOMMENDED LAND PATTERN



Note : Dimension D and E1 do not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 10 mil per side.



## Carrier Tape & Reel Dimensions

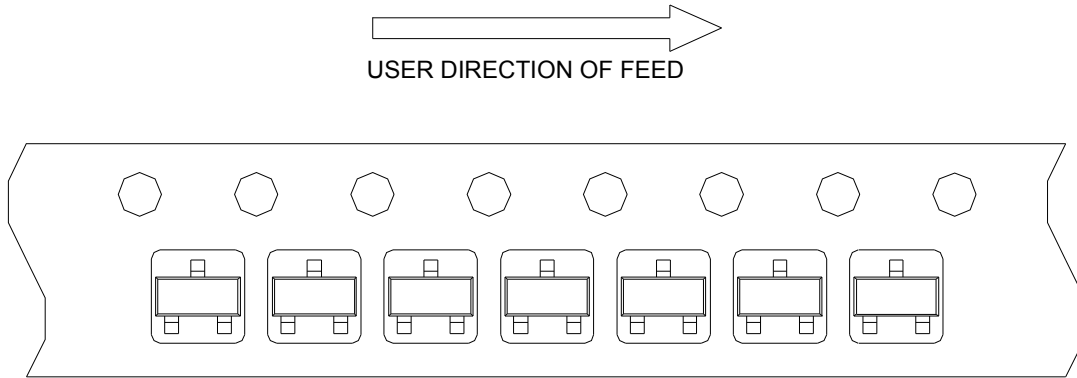


Application	A	H	T1	C	d	D	W	E1	F
SOT-23-3	178.0±2.00	50 MIN.	8.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	8.0±0.30	1.75±0.10	3.5±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0±0.10	4.0±0.10	2.0±0.05	1.5+0.10 -0.00	1.0 MIN.	0.6+0.00 -0.40	3.20±0.20	3.10±0.20	1.50±0.20

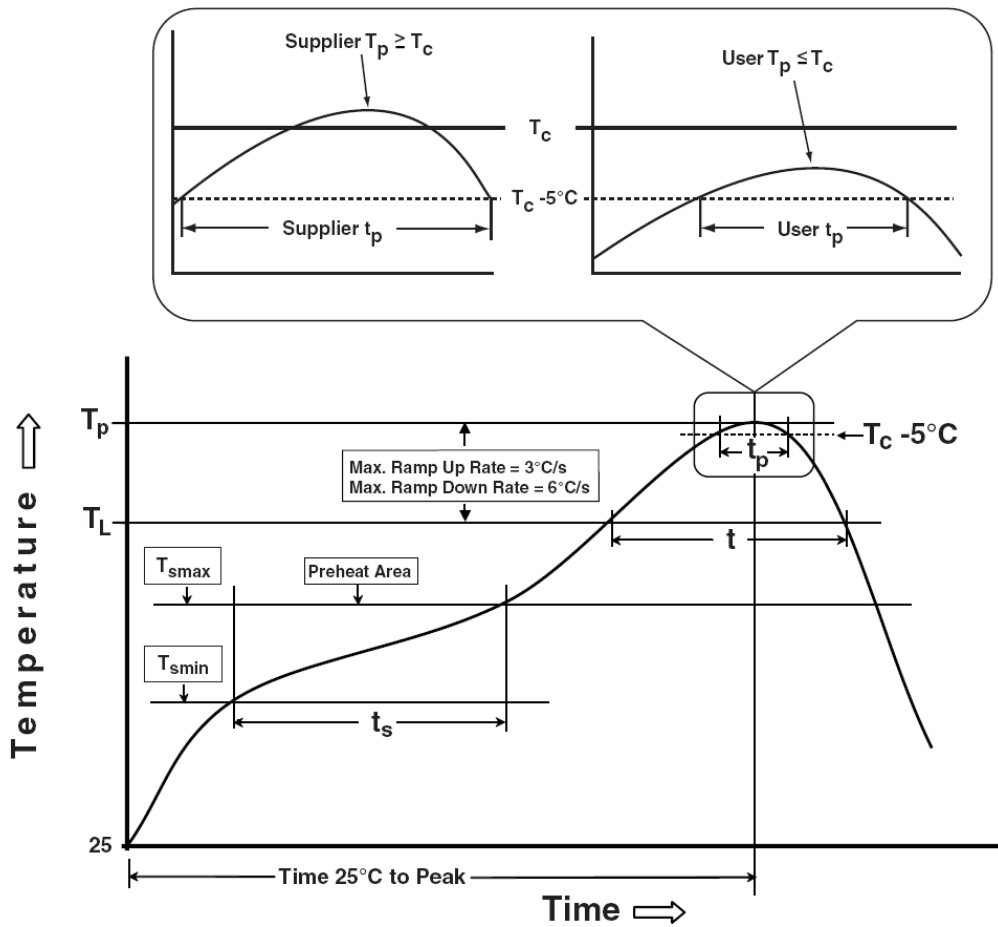
(mm)

## Taping Direction Information

SOT-23-3



## Classification Profile



## Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
<b>Preheat &amp; Soak</b>		
Temperature min ( $T_{smin}$ )	100 °C	150 °C
Temperature max ( $T_{smax}$ )	150 °C	200 °C
Time ( $T_{smin}$ to $T_{smax}$ ) ( $t_s$ )	60-120 seconds	60-120 seconds
Average ramp-up rate ( $T_{smax}$ to $T_p$ )	3 °C/second max.	3°C/second max.
Liquidous temperature ( $T_L$ )	183 °C	217 °C
Time at liquidous ( $t_L$ )	60-150 seconds	60-150 seconds
Peak package body Temperature ( $T_p$ )*	See Classification Temp in table 1	See Classification Temp in table 2
Time ( $t_p$ )** within 5°C of the specified classification temperature ( $T_c$ )	20** seconds	30** seconds
Average ramp-down rate ( $T_p$ to $T_{smax}$ )	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature ( $T_p$ ) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature ( $t_p$ ) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures ( $T_c$ )

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures ( $T_c$ )

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350-2000	Volume mm <sup>3</sup> >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

## Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ $T_{jmax}$
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ $T_{jmax}$
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

## Customer Service

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